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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Jammy et al.
Serial No.: 09/363,523
Filed: July 29, 1999
Entitled: Method For Forming Crystalline Silicon
Nitride

Group Art Unit: 2823
Examiner: M. ESTRADA
Docket No.: 99 P 7722 US
Batch No.: TBD

LETTER TO OFFICIAL DRAFTSMAN

Attention: Drawing Processing Branch
Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Pursuant to M.P.E.P. Section 608.02, enclosed please find five (5) sheets of formal drawings in the referenced case. These are formal versions of the informal drawings filed with the application.

If there are any informalities with these drawings, Applicant requests issuance of a Form PTO-948 identifying the informalities noted by the Official Draftsman.

Respectfully submitted,

Stanton C. Braden
Reg. No. 32,556

Date: December 10, 2001

Infineon Technologies North America Corp.
c/o Siemens Corporation
Intellectual Property Department
186 Wood Avenue South
Iselin, NJ 08830
(732) 321-3015
SCB/vl

CERTIFICATE OF MAILING PURSUANT TO 37 CFR § 1.8

I hereby certify that this correspondence is being deposited on or before the date, December 10, 2001 with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231

Date of Signature: December 10, 2001

Pamela J. Gewirtz